Abstract

Radiation-emitting thin-film semiconductor component based on GaN

The invention discloses a radiation-emitting thin-film semiconductor component with a multilayer structure (12) based on GaN, which contains an active, radiation-generating layer (14) and has a first main area (16) and a second main area (18) - remote from the first main area - for coupling out the radiation generated in the active, radiation-generating layer. Furthermore, the first main area (16) of the multilayer structure (12) is coupled to a reflective layer or interface, and the region (22) of the multilayer structure that adjoins the second main area (18) of the multilayer structure is patterned one- or two-dimensionally.

Figure 1